

Search History. 9/27/04. ~~9/27/04~~.. (9999)

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|---|------------------|
| 1 | 2 | ("6731531").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 15:23 |
| 2 | 4 | 258467.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 15:24 |
| 3 | 3 | 903453.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 15:25 |
| 4 | 5 | 461593.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 15:27 |
| 5 | 8 | 789203.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 15:45 |
| 6 | 9795 | 257/77.ccls. 257/314/ccls. 257/315.ccls. 257/316.ccls. 365/185.\$2.ccls. | USPAT; US-PGPUB | 2004/09/27 15:46 |
| 7 | 1700 | (257/77.ccls. 257/314/ccls. 257/315.ccls. 257/316.ccls. 365/185.\$2.ccls.) and floating adj gate near5 (sic silicon carbide "Si.sub."\$3"C.sub."\$3) | USPAT; US-PGPUB | 2004/09/27 15:46 |
| 8 | 36 | (257/77.ccls. 257/314/ccls. 257/315.ccls. 257/316.ccls. 365/185.\$2.ccls.) and floating adj gate near5 (sic silicon adj carbide "Si.sub."\$3"C.sub."\$3) | USPAT; US-PGPUB | 2004/09/27 15:47 |

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|----------------------|-----|---|---|------------------|
| 21 | 243 | (US-4852062-\$ or US-6100193-\$ or US-5990531-\$ or US-6166768-\$ or US-5336361-\$ or US-6271566-\$ or US-6049091-\$ or US-5861346-\$ or US-5828101-\$ or US-5910665-\$ or US-6703264-\$ or US-6228751-\$ or US-6141256-\$ or US-6009018-\$ or US-5754477-\$ or US-5719410-\$ or US-5670790-\$ or US-5672889-\$ or US-5698869-\$ or US-5714766-\$ or US-5640343-\$ or US-5654208-\$ or US-5661312-\$ or US-5625217-\$ or US-5629222-\$ or US-5562769-\$).did. or (US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5530581-\$ or US-5539217-\$ or US-5557114-\$ or US-5557122-\$ or US-5789276-\$ or US-5793697-\$ or US-5734181-\$ or US-5740104-\$ or US-4189826-\$ or US-4373167-\$ or US-4426764-\$ or US-4113515-\$ or US-4657699-\$ or US-4598305-\$ or US-4460670-\$ or US-4462150-\$ or US-4473836-\$ or US-4451391-\$ or US-4826778-\$ or US-4738729-\$ or US-4768072-\$ or US-4507673-\$ or US-5506421-\$ or US-5455432-\$).did. or (US-5465249-\$ or US-6108177-\$ or US-5369040-\$ or US-5393999-\$ or US-5371383-\$ or US-5323040-\$ or US-5298796-\$ or US-5293560-\$ or US-5260560-\$ or US-5260593-\$ or US-5159424-\$ or US-5235195-\$ or US-5145741-\$ or US-5061976-\$ or US-5111430-\$ or US-5049950-\$ or US-5039354-\$ or US-5056897-\$ or US-5477485-\$ or US-5449941-\$ or US-5451798-\$ or US-5407845-\$ or US-5408377-\$ or US-5415126-\$ or US-5441901-\$ or US-5449925-\$ or US-6099574-\$).did. or (US-5508543-\$ or US-6011279-\$ or US-5976926-\$ or US-5907775-\$ or US-5932902-\$ or US-5959896-\$ or US-5886368-\$ or US-5886376-\$ or US-5886379-\$ or US-5898197-\$ or US-5877041-\$ or US-5852306-\$ or US-5858811-\$ or US-5866930-\$ or US-5798548-\$ or US-5808336-\$ or US-5846859-\$ or US-5786250-\$ or US-6002143-\$ or US-5989958-\$ or US-6075259-\$ or US-6031263-\$ or US-6018166-\$ or US-5030580-\$ or US-4994401-\$ or US-4943838-\$ or US-4769686-\$).did. or (US-4841349-\$ or US-4849797-\$ or US-4893273-\$ or US-6133587-\$ or US-6141260-\$ or US-6144581-\$ or US-6049110-\$ or US-6034001-\$ or US-6125062-\$ or US-6180958-\$ or US-6246606-\$ or US-6236590-\$ or US-6178112-\$ or US-6166948-\$ or US-6197439-\$ or US-6140181-\$ or US-6166319-\$ or US-6163066-\$ or US-6166401-\$ or US-6133120-\$ or US-6130147-\$ or US-6084248-\$ or US-6093937-\$ or US-6754108-\$ or US-6121633-\$ or US-6313482-\$ or US-6309907-\$).did. or (US-6344663-\$ or US-6365919-\$ or US-6351411-\$ or US-6452831-\$ or US-6407426-\$ or US-6407424-\$ or US-6383576-\$ or US-6465375-\$ or US-6452839-\$ or US-6514820-\$ or US-6492684-\$ or US-6562131-\$ or US-6537371-\$ or US-6731531-\$ or US-6734510-\$ or US-6586797-\$ or | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/27 15:59 |
| Search History | | 9/27/04 4:56:49 PM | Page 4 | |
| H:\EASTBACK\09691004 | | USP | | |

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|----------------------|----|--|---|------------------|
| 22 | 70 | ((US-4852062-\$ or US-6100193-\$ or US-5990531-\$ or US-6166768-\$ or US-5336361-\$ or US-6271566-\$ or US-6049091-\$ or US-5861346-\$ or US-5828101-\$ or US-5910665-\$ or US-6703264-\$ or US-6228751-\$ or US-6141256-\$ or US-6009018-\$ or US-5754477-\$ or US-5719410-\$ or US-5670790-\$ or US-5672889-\$ or US-5698869-\$ or US-5714766-\$ or US-5640343-\$ or US-5654208-\$ or US-5661312-\$ or US-5625217-\$ or US-5629222-\$ or US-5562769-\$).did. or (US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5530581-\$ or US-5539217-\$ or US-5557114-\$ or US-5557122-\$ or US-5789276-\$ or US-5793697-\$ or US-5734181-\$ or US-5740104-\$ or US-4189826-\$ or US-4373167-\$ or US-4426764-\$ or US-4113515-\$ or US-4657699-\$ or US-4598305-\$ or US-4460670-\$ or US-4462150-\$ or US-4473836-\$ or US-4451391-\$ or US-4826778-\$ or US-4738729-\$ or US-4768072-\$ or US-4507673-\$ or US-5506421-\$ or US-5455432-\$).did. or (US-5465249-\$ or US-6108177-\$ or US-5369040-\$ or US-5393999-\$ or US-5371383-\$ or US-5323040-\$ or US-5298796-\$ or US-5293560-\$ or US-5260560-\$ or US-5260593-\$ or US-5159424-\$ or US-5235195-\$ or US-5145741-\$ or US-5061976-\$ or US-5111430-\$ or US-5049950-\$ or US-5039354-\$ or US-5056897-\$ or US-5477485-\$ or US-5449941-\$ or US-5451798-\$ or US-5407845-\$ or US-5408377-\$ or US-5415126-\$ or US-5441901-\$ or US-5449925-\$ or US-6099574-\$).did. or (US-5508543-\$ or US-6011279-\$ or US-5976926-\$ or US-5907775-\$ or US-5932902-\$ or US-5959896-\$ or US-5886368-\$ or US-5886376-\$ or US-5886379-\$ or US-5898197-\$ or US-5877041-\$ or US-5852306-\$ or US-5858811-\$ or US-5866930-\$ or US-5798548-\$ or US-5808336-\$ or US-5846859-\$ or US-5786250-\$ or US-6002143-\$ or US-5989958-\$ or US-6075259-\$ or US-6031263-\$ or US-6018166-\$ or US-5030580-\$ or US-4994401-\$ or US-4943838-\$ or US-4769686-\$).did. or (US-4841349-\$ or US-4849797-\$ or US-4893273-\$ or US-6133587-\$ or US-6141260-\$ or US-6144581-\$ or US-6049110-\$ or US-6034001-\$ or US-6125062-\$ or US-6180958-\$ or US-6246606-\$ or US-6236590-\$ or US-6178112-\$ or US-6166948-\$ or US-6197439-\$ or US-6140181-\$ or US-6166319-\$ or US-6163066-\$ or US-6166401-\$ or US-6133120-\$ or US-6130147-\$ or US-6084248-\$ or US-6093937-\$ or US-6754108-\$ or US-6121633-\$ or US-6313482-\$ or US-6309907-\$).did. or (US-6344663-\$ or US-6365919-\$ or US-6351411-\$ or US-6452831-\$ or US-6407426-\$ or US-6407424-\$ or US-6383576-\$ or US-6465375-\$ or US-6452839-\$ or US-6514820-\$ or US-6492694-\$ or US-6562131-\$ or US-6537371-\$ or US-6731531-\$ or US-6734510-\$ or US-6586797-\$ or | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 15:59 |
| Search History | | 9/27/04 15:59:49 PM Page 41 | | |
| H:\EASTBACK\09691004 | | USP | | |

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|---|-----|--|---|------------------|
| - | 13 | ((("4113515") or ("4473836") or ("5698869") or ("5858811") or ("5976926") or ("6031263") or ("6084248") or ("6093937") or ("6099574") or ("6130147") or ("6144581") or ("6163066") or ("6166401")).PN. | USPAT | 2004/09/25 14:16 |
| - | 13 | (US-6144581-\$ or US-6163066-\$ or US-6166401-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$).did. | USPAT | 2002/05/10 11:29 |
| - | 1 | hartstein.in. and low adj voltage adj memory.ti. | EPO | 2002/05/10 11:28 |
| - | 0 | jp-63289960\$-\$.did. | USPAT | 2002/05/10 11:30 |
| - | 0 | jp-363289960\$-\$.did. | USPAT | 2002/05/10 11:30 |
| - | 0 | jp-0363289960\$-\$.did. | USPAT | 2002/05/10 11:34 |
| - | 1 | takashi.in. and carrier near6 silicon adj substrate | USPAT | 2002/05/10 11:36 |
| - | 3 | takashi.in. and carrier near6 silicon adj substrate | JPO | 2002/05/10 11:38 |
| - | 38 | diamond adj layer near6 process | DERWENT | 2002/05/10 11:39 |
| - | 2 | (diamond adj layer near6 process) and silicon adj carbide | DERWENT | 2002/05/10 11:45 |
| - | 1 | takashi.in. and ito.in. and igfet | EPO | 2002/05/10 11:45 |
| - | 0 | jp-063219172\$-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 11:47 |
| - | 2 | jp-63219172\$-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:15 |
| - | 2 | jp-63289960\$-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 11:49 |
| - | 2 | jp-01115162\$-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 11:49 |
| - | 2 | jp-63181473\$-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 11:50 |
| - | 2 | jp-62122275\$-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 11:51 |
| - | 0 | jp-404056769\$-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 11:52 |
| - | 2 | jp-04056769\$-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:02 |
| - | 796 | (257/77).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:04 |

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|---|-----|---|---|------------------|
| - | 9 | ((257/77).CCLS.) and (x near12 silicon adj carbide) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:18 |
| - | 489 | silicon adj carbide and gate and x and source and drain | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:19 |
| - | 53 | silicon adj carbide.ti.ab. and gate and x and source and drain | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:26 |
| - | 162 | stoichiometric adj coefficient | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:26 |
| - | 11 | stoichiometric adj coefficient near x | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:26 |
| - | 30 | stoichiometric adj coefficient near12 x | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:28 |
| - | 0 | "si.sub.1-x.c.sub.x" and field adj effect adj transistor | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:30 |
| - | 0 | "si.sub.1-x.c.sub.x" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:29 |
| - | 57 | "si.sub.1-x" adj "c.sub.x" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 12:31 |
| - | 18 | "si.sub.1-x" adj "c.sub.x" and (mosfet or fet or nmosfet or pmosfet or field adj effect adj transistor or dtmosfet or gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 13:55 |
| - | 15 | "si.sub.1-x" adj "c.sub.x" and (mosfet or fet or nmosfet or pmosfet or field adj effect adj transistor or dtmosfet or (gate and (source or drain))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 13:57 |
| - | 179 | ((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:07 |
| - | 50 | ((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:15 |

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|---|------|---|---|------------------|
| - | 1 | ((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier adj energy | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:10 |
| - | 30 | ((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:24 |
| - | 0 | ((257/77).CCLS.) and ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:26 |
| - | 0 | ((257/77).CCLS.) and ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:20 |
| - | 0 | ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:20 |
| - | 0 | ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:20 |
| - | 0 | ((257/77).CCLS.) and ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:27 |
| - | 30 | ((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:49 |
| - | 30 | ((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) and x and (source same drain) and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:51 |
| - | 53 | ((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:52 |
| - | 2616 | (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:53 |

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|---|-----|---|---|------------------|
| - | 133 | (silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:54 |
| - | 133 | (silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near6 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 14:55 |
| - | 2 | ((silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near6 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 15:05 |
| - | 0 | ((("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 15:09 |
| - | 0 | ((("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near12 gate) near12 (x or y or a or b) and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 18:35 |
| - | 1 | ((("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near12 gate) near12 (x or y or a or b) and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 15:12 |
| - | 684 | (silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near12 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 15:13 |
| - | 161 | ((silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 18:42 |
| - | 2 | ("6249020").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 16:24 |
| - | 2 | ("6031263").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 17:09 |
| - | 2 | ("6049110").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 17:09 |

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| - | 0 | ((("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 18:33 |
| - | 0 | ((("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 18:33 |
| - | 51 | (US-5451798-\$ or US-6166319-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6144581-\$ or US-6163066-\$ or US-6166401-\$ or US-5661312-\$ or US-5719410-\$ or US-5798548-\$ or US-5801401-\$ or US-6011279-\$ or US-6049110-\$ or US-6306691-\$ or US-6313482-\$ or US-6365919-\$ or US-6249020-\$ or US-6344663-\$).did. or (US-5886368-\$ or US-6383576-\$ or US-4826778-\$ or US-5039354-\$ or US-5056897-\$ or US-5159424-\$ or US-5260560-\$ or US-5369040-\$).did. or (US-20010032997-\$ or US-20010049183-\$).did. or (EP-681333-\$ or EP-291951-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or JP-63181473-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-63289960-\$ or JP-56056677-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or EP-276002-\$ or EP-291951-\$ or JP-01115162-\$ or JP-07115191-\$).did. | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2002/05/10 18:34 |
| - | 351 | silicon near3 doped near6 carbon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 18:36 |
| - | 45 | (silicon near3 doped near6 carbon) and (257/\$6.ccls. or 438/\$6.ccls.) and gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 18:38 |
| - | 4 | ((silicon near3 doped near6 carbon) near12 gate) and (257/\$6.ccls. or 438/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 18:40 |
| - | 5 | ((silicon near3 dop\$3 near6 carbon) near12 gate) and (257/\$6.ccls. or 438/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 18:41 |
| - | 235 | ((carbon or silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 18:43 |

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| - | 74 | ((carbon or silicon adj carbide or sic or "si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si(x)c(l-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls.) not ((silicon adj carbide or sic or "si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si(x)c(l-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 20:13 |
| - | 0 | silicon-doped adj carbon adj (film or electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 20:13 |
| - | 0 | si-doped adj carbon adj (film or electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 20:14 |
| - | 201 | ((c or carbon) near (si or silicon)) adj (film or electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 20:15 |
| - | 10092 | ((c or carbon) near6 (si or silicon)) near6 (film or electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 20:16 |
| - | 3434 | (carbon near6 (si or silicon)) near6 (film or electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 20:16 |
| - | 118 | (carbon near1 (si or silicon)) near3 (film or electrode) and (257/\$6.ccls. or 438/\$6.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 21:21 |
| - | 0 | polysilicon/carbon near12 gate adj electrode | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 21:22 |
| - | 0 | "polysilicon/carbon" near12 gate adj electrode | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 21:22 |
| - | 0 | (polysilicon near1 carbon) near12 gate adj electrode | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 21:23 |
| - | 1 | (silicon near1 carbon) near12 gate adj electrode | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 21:49 |
| - | 6 | p-doped adj silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 21:30 |

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| - | 7 | P-dopant near12 carbon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/10 21:49 |
| - | 0 | carbon adj doping adj2 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 16:21 |
| - | 4 | silicon adj doping adj2 carbon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 16:27 |
| - | 0 | p-doped adj silicon adj carbon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 16:27 |
| - | 7 | p-doped adj2 silicon adj2 carbon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 16:28 |
| - | 1 | (p-doped or p-doping) near12 silicon adj carbon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 16:31 |
| - | 0 | "si.sub.1-x.c.sub.x" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 16:35 |
| - | 57 | "si.sub.1-x c.sub.x" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 16:43 |
| - | 0 | "si.sub.1-x c.sub.x" near20 (work adj function or workfunction) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 16:43 |
| - | 2 | "si.sub.1-x c.sub.x" near20 (barrier or work adj function or workfunction) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 16:48 |
| - | 1 | "si.sub.x c.sub.1-x" near20 (barrier or work adj function or workfunction) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 16:49 |
| - | 10 | "si.sub.1-x c.sub.x" near20 (electrode or conductivity or conduction) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 17:04 |
| - | 1 | ("si.sub.1-x c.sub.x" or "si.sub.x c.sub.1-x" or "si.sub.1-y c.sub.y" or "si.sub.y c.sub.1-y") near20 electron adj affinity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 20:09 |
| - | 0 | resistivity near4 "si.sub.1-x. c.x" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 20:26 |

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| - | 965 | (conductivity or resistivity) near12 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 20:39 |
| - | 0 | (conductivity or resistivity) near12 "si.sub.1-x c.x" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 21:10 |
| - | 8 | barrier adj energy near12 silicon adj dioxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 21:14 |
| - | 0 | barrier adj energy near12 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 21:20 |
| - | 108 | barrier adj energy.ti,ab. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 21:23 |
| - | 2 | barrier adj energy near12 (sic or "si.sub.1-x. c.x" or silicon adj carbide) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/11 21:24 |
| - | 21 | (resistivity or conductivity) near12 (silicon adj carbide or "si.sub.1-x. c.sub.x" or "si.sub.x. c.sub.1-x") near12 x | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 12:26 |
| - | 17 | barrier adj energy near12 gate near12 insulator | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 12:07 |
| - | 3 | ("5661312").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 12:10 |
| - | 0 | ("floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide)").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 12:10 |
| - | 30 | floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 12:11 |
| - | 0 | floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and photodetection | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 12:12 |
| - | 30 | floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 12:21 |
| - | 18 | floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory and barrier | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 12:21 |

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| - | 18 | floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory and (barrier adj energy or potential adj barrier or tunneling adj barrier or interface adj barrier or barrier) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 12:23 |
| - | 3 | ("5886368").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 17:44 |
| - | 3 | ("5661312").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 17:46 |
| - | 46061 | polycrystalline near12 silicon carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect\$3) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 17:48 |
| - | 13 | polycrystalline near12 silicon adj carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect\$3) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 17:50 |
| - | 22 | (polycrystalline or monocrystalline) near12 silicon adj carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect\$3) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 17:51 |
| - | 4 | (polycrystalline or monocrystalline) near12 silicon adj carbide near12 gate and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect\$3) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 17:52 |
| - | 24 | (polycrystalline or monocrystalline) near12 silicon adj carbide near12 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 18:16 |
| - | 3 | ("5369040").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 18:17 |
| - | 10 | floating adj gate near12 control adj gate and photodetect\$3 and (mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or transistor or field adj effect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 18:30 |
| - | 0 | floating adj gate near12 control adj gate near12 silicon adj carbide and photodetect\$3 and (mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or transistor or field adj effect) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 18:31 |
| - | 0 | floating adj gate near12 control adj gate near12 silicon adj carbide and photodetect\$3 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 18:31 |
| - | 0 | floating adj gate near12 control adj gate near12 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 18:32 |
| - | 2 | floating adj gate near12 control adj gate near12 (sic or silicon adj carbide or "si.sub.1-x. c.sub.x") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 18:56 |

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| - | 2 | ("5989958").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 19:00 |
| - | 3 | ("5801401").PN. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 19:33 |
| - | 2 | ("5808336").PN. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 19:43 |
| - | 3 | ("5801401").PN. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/12 19:43 |
| - | 3 | ("4473836").PN. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 10:06 |
| - | 2 | ("5808336").PN. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 10:11 |
| - | 3 | ("5801401").PN. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 11:25 |
| - | 0 | floating adj gate and control adj gate and source same drain and silcion adj carbide and silicon adj substrate and channel | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 11:26 |
| - | 41 | floating adj gate and control adj gate and source same drain and silicon adj carbide and silicon adj substrate and channel | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 11:27 |
| - | 41 | floating adj gate and control adj gate and source same drain and silicon adj carbide and silicon adj substrate and channel and (memory or photodetect\$3) | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 12:16 |
| - | 74 | crystalline near12 floating adj gate | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 12:16 |
| - | 37 | crystalline near3 floating adj gate | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 13:21 |
| - | 5 | ((("5661312") or ("5798548") or ("5989958") or ("5369040") or ("5557122"))).PN. | USPAT | 2002/05/13 16:23 |
| - | 47 | hamakawa.in. and carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 16:13 |
| - | 24 | hamakawa.in. and carbide | JPO | 2002/05/13 16:13 |
| - | 1 | ("5808336").PN. | USPAT | 2002/05/13 17:16 |

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|---|----|---|---|------------------|
| - | 52 | ((("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN. | USPAT | 2002/05/13 17:30 |
| - | 6 | ((("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.) and ("si.sub.1-x. c.sub.x" or "si.sub.1-y. c.sub.y" or "si.sub.x c.sub.1-x" or "si.sub.y c.sub.1-y" or silicon carbide or sic) and source and drain and floating adj gate and control adj gate and silicon adj dioxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 18:18 |

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| - | 0 | ((("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.) and ("si.sub.1-x. c.sub.x" or "si.sub.1-y. c.sub.y" or "si.sub.x c.sub.1-x" or "si.sub.y c.sub.1-y") and source and drain and floating adj gate and control adj gate and silicon adj dioxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 20:34 |
| - | 588 | (257/77).CCLS. | USPAT; US-PGPUB | 2002/05/13 20:34 |
| - | 118 | (257/153).CCLS. | USPAT; US-PGPUB | 2002/05/13 20:34 |
| - | 402 | (257/314).CCLS. | USPAT; US-PGPUB | 2002/05/13 20:39 |
| - | 782 | (257/315).CCLS. | USPAT; US-PGPUB | 2002/05/13 20:39 |
| - | 943 | (257/316).CCLS. | USPAT; US-PGPUB | 2002/05/13 20:40 |
| - | 2311 | ((257/77).CCLS.) or ((257/153).CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316).CCLS.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 20:40 |
| - | 357 | ((257/77).CCLS.) or ((257/153).CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316).CCLS.)) and silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 20:44 |
| - | 90 | ((257/77).CCLS.) or ((257/153).CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316).CCLS.)) and (silicon adj carbide near15 gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 21:12 |
| - | 2 | ("5989958").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/13 21:12 |

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| - | 115 | (US-5449941-\$ or US-5455432-\$ or US-5039354-\$ or US-5056897-\$ or US-5159424-\$ or US-5260560-\$ or US-5369040-\$ or US-5451798-\$ or US-5734181-\$ or US-6166319-\$ or US-6383576-\$ or US-5801401-\$ or US-5989958-\$ or US-6344663-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6144581-\$ or US-6163066-\$).did. or (US-6166401-\$ or US-5465249-\$ or US-4451391-\$ or US-6309907-\$ or US-5061976-\$ or US-5625217-\$ or US-5661312-\$ or US-5798548-\$ or US-6011279-\$ or US-6049110-\$ or US-6249020-\$ or US-6306691-\$ or US-6313482-\$ or US-6365919-\$ or US-5719410-\$ or US-5886368-\$ or US-4826778-\$ or US-6351411-\$ or US-5557114-\$ or US-5562769-\$ or US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5629222-\$ or US-5654208-\$ or US-5670790-\$ or US-5714766-\$).did. or (US-5740104-\$ or US-5754477-\$ or US-5786250-\$ or US-5789276-\$ or US-5846859-\$ or US-5877041-\$ or US-5886379-\$ or US-5907775-\$ or US-6018166-\$ or US-6034001-\$ or US-6075259-\$ or US-5557122-\$ or US-5866930-\$ or US-5898197-\$ or US-5808336-\$ or US-5393999-\$ or US-5539217-\$ or US-4460670-\$ or US-4462150-\$ or US-4507673-\$ or US-4657699-\$ or US-4738729-\$ or US-4768072-\$ or US-4769686-\$ or US-4841349-\$ or US-4849797-\$ or US-4893273-\$).did. or (US-5049950-\$ or US-5111430-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$ or US-5293560-\$ or US-5298796-\$ or US-5371383-\$ or US-5407845-\$ or US-5415126-\$ or US-5508543-\$ or US-5530581-\$ or US-5477485-\$).did. or (US-20010032997-\$ or US-20010049183-\$ or US-20020024050-\$ or US-20020017647-\$).did. or (EP-291951-\$ or EP-681333-\$).did. or (JP-62122275-\$ or JP-63181473-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-04056769-\$ or JP-63289960-\$ or JP-57126175-\$ or JP-04061170-\$ or JP-56056677-\$ or JP-02203564-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or JP-01115162-\$ or EP-291951-\$ or EP-276002-\$ or JP-07115191-\$).did. | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2002/05/14 08:24 |
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| - | 1 | ((US-5449941-\$ or US-5455432-\$ or US-5039354-\$ or US-5056897-\$ or US-5159424-\$ or US-5260560-\$ or US-5369040-\$ or US-5451798-\$ or US-5734181-\$ or US-6166319-\$ or US-6383576-\$ or US-5801401-\$ or US-5989958-\$ or US-6344663-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6144581-\$ or US-6163066-\$).did. or (US-6166401-\$ or US-5465249-\$ or US-4451391-\$ or US-6309907-\$ or US-5061976-\$ or US-5625217-\$ or US-5661312-\$ or US-5798548-\$ or US-6011279-\$ or US-6049110-\$ or US-6249020-\$ or US-6306691-\$ or US-6313482-\$ or US-6365919-\$ or US-5719410-\$ or US-5886368-\$ or US-4826778-\$ or US-6351411-\$ or US-5557114-\$ or US-5562769-\$ or US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5629222-\$ or US-5654208-\$ or US-5670790-\$ or US-5714766-\$).did. or (US-5740104-\$ or US-5754477-\$ or US-5786250-\$ or US-5789276-\$ or US-5846859-\$ or US-5877041-\$ or US-5886379-\$ or US-5907775-\$ or US-6018166-\$ or US-6034001-\$ or US-6075259-\$ or US-5557122-\$ or US-5866930-\$ or US-5898197-\$ or US-5808336-\$ or US-5393999-\$ or US-5539217-\$ or US-4460670-\$ or US-4462150-\$ or US-4507673-\$ or US-4657699-\$ or US-4738729-\$ or US-4768072-\$ or US-4769686-\$ or US-4841349-\$ or US-4849797-\$ or US-4893273-\$).did. or (US-5049950-\$ or US-5111430-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$ or US-5293560-\$ or US-5298796-\$ or US-5371383-\$ or US-5407845-\$ or US-5415126-\$ or US-5508543-\$ or US-5530581-\$ or US-5477485-\$).did. or (US-20010032997-\$ or US-20010049183-\$ or US-20020024050-\$ or US-20020017647-\$).did. or (EP-291951-\$ or EP-681333-\$).did. or (JP-62122275-\$ or JP-63181473-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-04056769-\$ or JP-63289960-\$ or JP-57126175-\$ or JP-04061170-\$ or JP-56056677-\$ or JP-02203564-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or JP-01115162-\$ or EP-291951-\$ or EP-276002-\$ or JP-07115191-\$).did.) and ohba.in. (257/77).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/14 08:34 |
| - | 799 | | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/14 08:53 |
| - | 2 | ("5989958").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/14 10:54 |

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| - | 469 | (257/314).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 09:08 |
| - | 467 | ((257/314).CCLS.) not ((257/77).CCLS.) | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 09:24 |
| - | 1816 | 257/315 | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 09:24 |
| - | 1577 | (257/315 not (((257/314).CCLS.) not ((257/77).CCLS.))) not ((257/77).CCLS.) | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 09:26 |
| - | 1375 | (257/316).CCLS. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 10:54 |
| - | 858 | ((((257/316).CCLS.) not 257/315) not (((257/314).CCLS.) not ((257/77).CCLS.))) not ((257/77).CCLS.) | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 10:55 |
| - | 0 | ("jp-3222367\$-\$\$.did.").PN. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:45 |
| - | 2 | jp-03222367\$-\$\$.did. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:46 |
| - | 13 | jp-0224431\$-\$\$.did. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:46 |
| - | 2 | jp-06224431\$-\$\$.did. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:47 |
| - | 10 | jp-302828\$-\$\$.did. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:48 |
| - | 2 | jp-06302828\$-\$\$.did. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:48 |
| - | 2 | jp-07226507\$-\$\$.did. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:49 |
| - | 2 | jp-08255878\$-\$\$.did. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:50 |

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| - | 0 | jp-08255878TR\$-\$\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:50 |
| - | 0 | jp-08255878-TR\$-\$\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:50 |
| - | 2 | jp-60184681\$-\$\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:52 |
| - | 2 | jp-60242678\$-\$\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 12:52 |
| - | 4 | method adj2 using.clm. and optical adj switch.ti. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/14 13:29 |
| - | 714 | (257/295).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/15 13:13 |
| - | 0 | ("mram.ti,ab.").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/15 13:13 |
| - | 276 | mram.ti,ab. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/15 13:21 |
| - | 988 | ((257/295).CCLS.) or mram.ti,ab. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/15 13:21 |
| - | 873 | magnetic adj memory adj device | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/15 13:32 |
| - | 4 | ((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj (layer or film) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/15 13:38 |
| - | 8 | ((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj2 (layer or film) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/15 14:56 |
| - | 1 | ((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj2 (layer or film) same orient\$5 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/15 15:06 |
| - | 1846 | ((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/15 17:14 |

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| - | 2 | ((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 15:51 |
| - | 1 | ((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented) and coercivity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 15:59 |
| - | 0 | ((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented) and coercivity and ferrimagnetic | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 17:01 |
| - | 719 | ((257/295).CCLS.) or (magnetic adj memory adj device) and af adj layer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 17:17 |
| - | 44 | (365/172).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 17:35 |
| - | 283 | (365/173).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 17:35 |
| - | 804 | ((365/171) or (365/172) or (365/173)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 18:02 |
| - | 0 | ((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity and (data adj storage near3 (layer or film)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 18:08 |
| - | 4 | ((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity | USPAT; US-PGPUB | 2002/05/15 18:10 |
| - | 4 | ((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation) | USPAT; US-PGPUB | 2002/05/15 19:32 |
| - | 0 | ((365/171) or (365/172) or (365/173)).CCLS.) and ((synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic) near6 (layer or film)) | USPAT; US-PGPUB | 2002/05/15 18:31 |
| - | 0 | ((365/171) or (365/172) or (365/173)).CCLS.) and (synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic) | USPAT; US-PGPUB | 2002/05/15 18:31 |
| - | 23 | (synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic) and (mram or magnetic adj memory) | USPAT; US-PGPUB | 2002/05/15 18:36 |
| - | 2 | (synthetic adj (ferrimagnet or ferrimagnetic) or sf or artificial adj ferrimagnetic) and (mram or magnetic adj memory).ti,ab. | USPAT; US-PGPUB | 2002/05/15 18:38 |

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| - | 4 | ((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation) | USPAT; US-PGPUB | 2002/05/15 19:44 |
| - | 4 | (antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation) | USPAT; US-PGPUB | 2002/05/15 19:46 |
| - | 4 | (antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 19:48 |
| - | 4 | (antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 19:48 |
| - | 17 | (antiferrimagnetic or femn or af) and (magnetic adj memory) and coercivity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 19:51 |
| - | 8934 | (antiferrimagnetic or femn or af) and (hs mtj or hard-soft adj mtj) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 19:52 |
| - | 1 | (antiferrimagnetic or femn or af) and (hs adj mtj or hard-soft adj mtj) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 21:17 |
| - | 1 | "5966012".PN. | USPAT | 2002/05/15 20:52 |
| - | 1 | "5841692".PN. | USPAT | 2002/05/15 20:55 |
| - | 1 | "5801984".PN. | USPAT | 2002/05/15 20:56 |
| - | 1 | "5055158".PN. | USPAT | 2002/05/15 20:57 |
| - | 1 | "5055158".PN. | USPAT | 2002/05/15 20:58 |
| - | 1 | (antiferromagnetic or femn or af) and (hs adj mtj or hard-soft adj mtj) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 21:24 |
| - | 2 | ("5605958").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 21:24 |
| - | 3 | ("5650958").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 22:05 |
| - | 77 | magnetic adj memory and spacer adj layer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 22:29 |
| - | 0 | magnetic adj memory and (spacer adj layer near12 sf) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/15 22:30 |

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| - | 77 | magnetic adj memory and spacer adj layer | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/15 22:48 |
| - | 7 | magnetic adj memory and (spacer adj layer near5 antiferromagnetic) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 07:45 |
| - | 3 | magnetic adj memory and (spacer adj layer near5 antiferromagnetic) and (spacer near12 different) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:01 |
| - | 0 | (spacer near12 antiferromagnetic near12 different) and magnetic adj2 memory | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:02 |
| - | 5 | spacer near12 antiferromagnetic near12 different | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:45 |
| - | 295 | (365/158).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:45 |
| - | 602 | (365/171).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:46 |
| - | 44 | (365/172).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:46 |
| - | 283 | (365/173).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:46 |
| - | 3429 | (365/174).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:46 |
| - | 431 | (257/30).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:47 |
| - | 4807 | ((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:47 |
| - | 179 | spacer and coercivity and antiferromagnetic | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 08:48 |
| - | 11 | ((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.) and (spacer and coercivity and antiferromagnetic) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/05/16 13:56 |

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|---|-----|--|---|------------------|
| - | 5 | ((((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.)) and (spacer and coercivity and antiferromagnetic)) and @pd<20000104 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 14:30 |
| - | 0 | mtj adj mr and world adj line and bottom adj electrode | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 14:31 |
| - | 0 | mtj adj mr and world adj line | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 14:32 |
| - | 1 | mtj adj mr and word adj line | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 14:33 |
| - | 7 | "6114719" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 15:30 |
| - | 3 | mtj and (current near12 (magnetization or magnetized)) near12 (perpendicular or orthogonal) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 16:37 |
| - | 0 | "not pinned" and (mram or mtj) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 16:44 |
| - | 0 | "not pinned" and (mram or mtj or magneto-resistive or af adj layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 16:45 |
| - | 178 | (hard same soft) and (mram or mtj or magneto-resistive or af adj layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 16:47 |
| - | 0 | (soft-soft) and (mram or mtj or magneto-resistive or af adj layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 16:47 |
| - | 0 | soft-soft and (mtj or mram or magneto-resistive) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 16:49 |
| - | 11 | soft-soft | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 16:50 |
| - | 0 | soft-soft and magnetic | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 16:50 |
| - | 3 | mtj and second adj free | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/05/16 20:54 |

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| - | 17 | (spacer near12 (ru or ruthenium)) near12 (af adj layer reference adj layer or data adj layer or sens\$3 adj layer or pinned adj2 layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/05/16 22:40 |
| - | 3 | ((("5640343") or ("6269018") or ("5966012"))).PN. | | 2002/05/16 23:13 |
| - | 2 | 903452.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 11:23 |
| - | 2 | ("5989958").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 12:57 |
| - | 0 | jp-03571261\$-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 12:58 |
| - | 8 | hamakawa.in. and silicon and carbide and semiconductor | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB JPO | 2002/11/04 13:00 |
| - | 2 | "3571261" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 12:59 |
| - | 1 | "carbide/amorphous".ti. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 15:49 |
| - | 0 | optoelectric adj conversion and electron adj affinity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 18:04 |
| - | 329 | optoelectric adj conversion | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 18:04 |
| - | 2724 | electron adj affinity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 18:04 |
| - | 0 | optoelectric adj conversion near12 affinity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 18:05 |
| - | 32 | optoelectric adj conversion near12 efficiency | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 18:06 |
| - | 4 | optoelectric adj conversion near12 efficiency and silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPÄT | 2002/11/04 18:07 |
| - | 3404 | ((257/77) or (257/314) or (257/315) or (257/316)).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/05 11:44 |

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| - | 14 | ((257/77) or (257/314) or (257/315) or (257/316)).CCLS.) and breakdown adj voltage near15 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/05 11:46 |
| - | 1 | ((257/77) or (257/314) or (257/315) or (257/316)).CCLS.) and electron adj affinity near15 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/05 11:47 |
| - | 2 | ("6104054").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/11/05 14:24 |
| - | 8 | ("5661312") or ("5798548") or ("5989958") or ("5808336") or ("5369040") or ("5557122") or ("5393999") or ("5734181").PN. | USPAT | 2003/01/27 10:34 |
| - | 0 | jp-357126175\$-\$\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/27 10:38 |
| - | 2 | jp-57126175\$-\$\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/27 10:40 |
| - | 2 | jp-02203564\$-\$\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/01/27 10:40 |
| - | 13 | (US-6084248-\$ or US-6031263-\$ or US-5976926-\$ or US-5858811-\$ or US-5698869-\$ or US-4473836-\$ or US-4113515-\$ or US-6130147-\$ or US-6144581-\$ or US-6099574-\$ or US-6093937-\$ or US-6166401-\$ or US-6163066-\$).did. | USPAT | 2003/03/21 13:50 |
| - | 57 | hamakawa.in. and conversion | USPAT; JPO | 2003/03/21 13:51 |
| - | 0 | hamakawa.in. and conversion and optoelectronic | JPO | 2003/03/21 13:51 |
| - | 1 | hamakawa.in. and conversion and heterojunction | JPO | 2003/03/21 13:52 |
| - | 31 | hamakawa.in. and conversion | JPO | 2003/03/21 13:52 |

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|---|-----|---|---|------------------|
| - | 141 | (US-5449941-\$ or US-6383576-\$ or US-6166319-\$ or US-5451798-\$ or US-5734181-\$ or US-5260560-\$ or US-5886379-\$ or US-5786250-\$ or US-5877041-\$ or US-5846859-\$ or US-5789276-\$ or US-5754477-\$ or US-5740104-\$ or US-5670790-\$ or US-5714766-\$ or US-5654208-\$ or US-5623442-\$ or US-5580380-\$ or US-5604357-\$ or US-5562769-\$ or US-5557114-\$ or US-5530581-\$ or US-5477485-\$ or US-5455432-\$ or US-5407845-\$ or US-5415126-\$).did. or (US-5298796-\$ or US-5293560-\$ or US-5260593-\$ or US-5235195-\$ or US-5145741-\$ or US-5111430-\$ or US-5049950-\$ or US-4893273-\$ or US-4841349-\$ or US-4769686-\$ or US-4738729-\$ or US-4657699-\$ or US-4462150-\$ or US-4460670-\$ or US-6002143-\$ or US-5852306-\$ or US-4849797-\$ or US-5369040-\$ or US-5039354-\$ or US-5159424-\$ or US-5056897-\$ or US-4826778-\$ or US-5886368-\$ or US-5719410-\$ or US-5371383-\$ or US-6236590-\$ or US-6166948-\$).did. or (US-5793697-\$ or US-5640343-\$ or US-6205052-\$ or US-6178112-\$ or US-6197439-\$ or US-6108177-\$ or US-5408377-\$ or US-6365919-\$ or US-6313482-\$ or US-6306691-\$ or US-6249020-\$ or US-6018166-\$ or US-6133587-\$ or US-6121633-\$ or US-6075259-\$ or US-6049110-\$ or US-6011279-\$ or US-5798548-\$ or US-5661312-\$ or US-5539217-\$ or US-5465249-\$ or US-5323040-\$ or US-4507673-\$ or US-5625217-\$ or US-5061976-\$ or US-6344663-\$ or US-6180958-\$).did. or (US-5989958-\$ or US-5801401-\$ or US-5393999-\$ or US-5629222-\$ or US-6309907-\$ or US-4768072-\$ or US-4451391-\$ or US-6351411-\$ or US-5898197-\$ or US-5508543-\$ or US-5808336-\$ or US-5866930-\$ or US-5557122-\$ or US-6034001-\$ or US-5907775-\$ or US-6166401-\$ or US-6163066-\$ or US-6144581-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6031263-\$ or US-6084248-\$ or US-5976926-\$ or US-5698869-\$ or US-4113515-\$ or US-4473836-\$).did. or (US-5858811-\$).did. or (US-20020017647-\$ or US-20020036331-\$ or US-20020041514-\$ or US-20020024050-\$ or US-20010049183-\$ or US-20010032997-\$).did. or (EP-291951-\$ or US-5585986-\$ or EP-681333-\$).did. or (JP-63219172-\$ or JP-01115162-\$ or JP-06302828-\$ or JP-07226507-\$ or JP-08255878-\$ or JP-60184681-\$ or JP-60242678-\$ or JP-63181473-\$ or JP-62122275-\$ or JP-04056769-\$ or JP-03222367-\$ or JP-02203564-\$ or JP-56056677-\$ or JP-04061170-\$ or JP-57126175-\$ or JP-06224431-\$ or JP-63289960-\$).did. or (EP-276002-\$ or JP-07115191-\$ or JP-62122275-\$ or JP-60184681-\$ or JP-01115162-\$ or JP-04056769-\$ or US-6081446-\$ or EP-291951-\$).did. | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2003/03/25 11:00 |
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| - | 1 | ((US-5449941-\$ or US-6383576-\$ or US-6166319-\$ or US-5451798-\$ or US-5734181-\$ or US-5260560-\$ or US-5886379-\$ or US-5786250-\$ or US-5877041-\$ or US-5846859-\$ or US-5789276-\$ or US-5754477-\$ or US-5740104-\$ or US-5670790-\$ or US-5714766-\$ or US-5654208-\$ or US-5623442-\$ or US-5580380-\$ or US-5604357-\$ or US-5562769-\$ or US-5557114-\$ or US-5530581-\$ or US-5477485-\$ or US-5455432-\$ or US-5407845-\$ or US-5415126-\$).did. or (US-5298796-\$ or US-5293560-\$ or US-5260593-\$ or US-5235195-\$ or US-5145741-\$ or US-5111430-\$ or US-5049950-\$ or US-4893273-\$ or US-4841349-\$ or US-4769686-\$ or US-4738729-\$ or US-4657699-\$ or US-4462150-\$ or US-4460670-\$ or US-6002143-\$ or US-5852306-\$ or US-4849797-\$ or US-5369040-\$ or US-5039354-\$ or US-5159424-\$ or US-5056897-\$ or US-4826778-\$ or US-5886368-\$ or US-5719410-\$ or US-5371383-\$ or US-6236590-\$ or US-6166948-\$).did. or (US-5793697-\$ or US-5640343-\$ or US-6205052-\$ or US-6178112-\$ or US-6197439-\$ or US-6108177-\$ or US-5408377-\$ or US-6365919-\$ or US-6313482-\$ or US-6306691-\$ or US-6249020-\$ or US-6018166-\$ or US-6133587-\$ or US-6121633-\$ or US-6075259-\$ or US-6049110-\$ or US-6011279-\$ or US-5798548-\$ or US-5661312-\$ or US-5539217-\$ or US-5465249-\$ or US-5323040-\$ or US-4507673-\$ or US-5625217-\$ or US-5061976-\$ or US-6344663-\$ or US-6180958-\$).did. or (US-5989958-\$ or US-5801401-\$ or US-5393999-\$ or US-5629222-\$ or US-6309907-\$ or US-4768072-\$ or US-4451391-\$ or US-6351411-\$ or US-5898197-\$ or US-5508543-\$ or US-5808336-\$ or US-5866930-\$ or US-5557122-\$ or US-6034001-\$ or US-5907775-\$ or US-6166401-\$ or US-6163066-\$ or US-6144581-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6031263-\$ or US-6084248-\$ or US-5976926-\$ or US-5698869-\$ or US-4113515-\$ or US-4473836-\$).did. or (US-5858811-\$).did. or (US-20020017647-\$ or US-20020036331-\$ or US-20020041514-\$ or US-20020024050-\$ or US-20010049183-\$ or US-20010032997-\$).did. or (EP-291951-\$ or US-5585986-\$ or EP-681333-\$).did. or (JP-63219172-\$ or JP-01115162-\$ or JP-06302828-\$ or JP-07226507-\$ or JP-08255878-\$ or JP-60184681-\$ or JP-60242678-\$ or JP-63181473-\$ or JP-62122275-\$ or JP-04056769-\$ or JP-03222367-\$ or JP-02203564-\$ or JP-56056677-\$ or JP-04061170-\$ or JP-57126175-\$ or JP-06224431-\$ or JP-63289960-\$).did. or (EP-276002-\$ or JP-07115191-\$ or JP-62122275-\$ or JP-60184681-\$ or JP-01115162-\$ or JP-04056769-\$ or US-6081446-\$ or EP-291951-\$).did.) and miyawaki.in. | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2003/03/25 11:00 |
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| - | 1 | ("4460670").PN. | USPAT | 2003/03/25 17:05 |
| - | 1 | ("4462150").PN. | USPAT | 2003/03/25 17:05 |
| - | 10 | (transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/18 17:38 |
| - | 11 | (transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/18 17:35 |
| - | 1 | ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y))) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/18 17:35 |
| - | 8 | gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)) and 257/\$9.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/18 17:40 |
| - | 0 | (gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)) and 257/\$9.ccls.) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/18 17:39 |
| - | 10 | gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/18 17:40 |
| - | 0 | (gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/18 18:18 |
| - | 2 | ("5661312").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 09:13 |
| - | 0 | ("jp-57125175\$-\$\$.did.").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 09:14 |
| - | 0 | jp-57125175\$-\$\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 09:14 |
| - | 2 | jp-57126175\$-\$\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 10:49 |
| - | 229 | barrier near6 gate and silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 09:35 |
| - | 5 | barrier near6 gate near6 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 10:02 |

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| - | 1 | "5506421".PN. | USPAT | 2003/08/19 09:37 |
| - | 1 | "5495124".PN. | USPAT | 2003/08/19 09:39 |
| - | 1 | "5451797".PN. | USPAT | 2003/08/19 09:39 |
| - | 1 | "5396085".PN. | USPAT | 2003/08/19 09:43 |
| - | 1 | "5393999".PN. | USPAT | 2003/08/19 09:45 |
| - | 15 | gate near6 breakdown near6 (silicon adj carbide "Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 10:12 |
| - | 304 | "Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 10:13 |
| - | 12 | ("Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x") and gate near6 breakdown | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 10:14 |
| - | 2 | ("5369040").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 10:58 |
| - | 0 | ("MOSadjphotodetector.ti,ab.").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 10:58 |
| - | 8 | MOS adj photodetector.ti,ab. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 11:50 |
| - | 17 | gate near6 polysilicon near6 carbon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 12:12 |
| - | 1 | "4963953".PN. | USPAT | 2003/08/19 12:03 |
| - | 1 | "4780394".PN. | USPAT | 2003/08/19 12:04 |
| - | 1 | "4352237".PN. | USPAT | 2003/08/19 12:04 |
| - | 1 | "4189826".PN. | USPAT | 2003/08/19 12:04 |
| - | 4 | ("3497773" "3622382" "3728590" "3896485").PN. | USPAT | 2003/08/19 12:07 |
| - | 43 | 3896485.URPN. | USPAT | 2003/08/19 12:07 |
| - | 1 | MOS adj photodetector.ti,ab,clm. and source and channel and drain | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 12:13 |
| - | 1 | (MOS MOSFET) adj photodetector.ti,ab,clm. and source and channel and drain | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 12:16 |
| - | 395 | photodetector.ti,ab,clm. and source and channel and drain | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 12:17 |
| - | 100 | photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 12:17 |
| - | 0 | photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 (sic silicon adj carbide) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 12:19 |

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| - | 1 | photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 polysilicon | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 12:23 |
| - | 7 | photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 (silicon polysilicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 13:12 |
| - | 2 | ("5808336").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 13:13 |
| - | 51 | floating adj gate and photodetector and source and drain and channel | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 13:55 |
| - | 65 | double-poly near12 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 15:12 |
| - | 0 | "4963953".PN. | USPAT | 2003/08/19 15:07 |
| - | 21 | ((("3792465") or ("4118795") or ("4384349") or ("4816883") or ("4897710") or ("5317535") or ("5366713") or ("5388069") or ("5424993") or ("5438544") or ("5441901") or ("5467306") or ("5493140") or ("5672889") or ("5828101") or ("5861346") or ("5912837") or ("5926740") or ("6297521") or ("6307775") or ("6309907"))).PN. | USPAT | 2003/08/19 15:29 |
| - | 9 | ((("3792465") or ("4118795") or ("4384349") or ("4816883") or ("4897710") or ("5317535") or ("5366713") or ("5388069") or ("5424993") or ("5438544") or ("5441901") or ("5467306") or ("5493140") or ("5672889") or ("5828101") or ("5861346") or ("5912837") or ("5926740") or ("6297521") or ("6307775") or ("6309907"))).PN.) and (silicon adj carbide or carbon near3 (polysilicon silicon)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 16:01 |
| - | 122 | silicon adj carbide and monocrystalline and power adj2 (MOS MOSFET device) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 16:02 |
| - | 59 | silicon adj carbide near12 monocrystalline and power adj2 (MOS MOSFET device) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 16:02 |
| - | 13 | silicon adj carbide near12 monocrystalline and power adj2 (MOS MOSFET device).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 16:04 |
| - | 1430 | silicon adj carbide near6 (MOS MOSFET device).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 16:05 |
| - | 111 | silicon adj carbide near6 power near6 (MOS MOSFET device).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 16:05 |

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| - | 55 | silicon adj carbide near6 power near6 (MOS MOSFET).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 16:05 |
| - | 6 | silicon adj carbide near6 power near6 (MOS MOSFET).ti,ab,clm. and monocrystalline near6 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 16:15 |
| - | 1811 | amorphous adj silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 16:16 |
| - | 73 | amorphous adj silicon adj carbide and grain adj size | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 16:16 |
| - | 2 | amorphous adj silicon adj carbide near12 grain adj size | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 16:32 |
| - | 23 | epitaxial\$2 near12 silicon adj carbide near12 method and (monocrystal monocrystalline) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 16:34 |
| - | 5 | epitaxial\$2 near12 silicon adj carbide near12 method near12 (monocrystal monocrystalline) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 16:35 |
| - | 463 | method near12 epitaxial\$2 near12 (monocrystal monocrystalline) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 16:38 |
| - | 112 | method near12 epitaxial\$2 near12 (monocrystal monocrystalline) and 117/\$6.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 16:59 |
| - | 112 | method near12 epitaxial\$2 near12 crystallinity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 16:59 |
| - | 0 | method near12 epitaxial\$2 near12 crystallinity and silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 17:00 |
| - | 0 | method near12 epitaxial\$2 near12 ensur\$3 near12 crystallinity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 17:00 |
| - | 49 | monocrystalline near4 silicon adj carbide and power.ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 17:01 |
| - | 2 | monocrystalline near4 silicon adj carbide near6 breakdown and power.ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 17:02 |

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| - | 2 | ("5,449,925").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:02 |
| - | 2 | ("5449925").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:03 |
| - | 1 | (("5449925").PN.) and epitaxial\$3 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:05 |
| - | 10 | epitaxial\$3 near6 grow\$3 near6 monocrystalline near6 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:08 |
| - | 14 | grow\$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:08 |
| - | 3 | method near6 grow\$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:09 |
| - | 1 | method near6 grow\$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm. and power.ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:09 |
| - | 16 | method near6 (growth growing) near6 (monocrystalline monocystal) near12 (silicon adj carbide sic) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:11 |
| - | 13 | method near6 (growth growing) near6 (monocrystalline monocystal) near12 (silicon adj carbide sic) and epitaxial\$2 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:20 |
| - | 2 | jp-57126175\$-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:25 |
| - | 13 | epitaxy near6 (grain crystal) adj size | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:39 |
| - | 4 | (work adj function workfunction) near12 crystallinity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:41 |
| - | 184995 | (work adj function workfunction) near12 silicon carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:41 |
| - | 15 | (work adj function workfunction) near12 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/19 17:43 |

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| - | 15 | (work adj function workfunction) near12 crystalline near6 amorphous | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 17:58 |
| - | 0 | ("carbonadjgate").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 17:59 |
| - | 9657 | gate adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 17:59 |
| - | 0 | carbon adj gate and source and drain | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 18:00 |
| - | 23 | carbon adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 18:00 |
| - | 19 | carbon adj gate and (257/\$9.ccls. 117/\$9.ccls. 438/\$9.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 18:03 |
| - | 14 | "carbon gate" and (257/\$9.ccls. 117/\$9.ccls. 438/\$9.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/19 18:04 |
| - | 63 | ("si.sub.x" adj "c.sub.1-x" or "si.sub.1-x" adj "c.sub.x") and (energy adj gap or band adj energy) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/20 10:00 |
| - | 132 | nanocrystalline and amorphous and silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/20 11:47 |
| - | 0 | nanocrystalline near20 amorphous near20 silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/20 11:47 |
| - | 4 | nanocrystalline same amorphous same silicon adj carbide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/20 12:23 |

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| - | 157 | (US-6121633-\$ or US-6133587-\$ or US-6297521-\$ or US-6306691-\$ or US-6313482-\$ or US-6249020-\$ or US-6365919-\$ or US-6075259-\$ or US-5323040-\$ or US-6130147-\$ or US-5698869-\$ or US-5465249-\$ or US-4113515-\$ or US-4849797-\$ or US-4507673-\$ or US-6031263-\$ or US-5858811-\$ or US-6011279-\$ or US-6049110-\$ or US-5976926-\$ or US-4473836-\$ or US-5734181-\$ or US-6383576-\$ or US-5449941-\$ or US-5393999-\$ or US-5629222-\$).did. or (US-5801401-\$ or US-6166401-\$ or US-6018166-\$ or US-5989958-\$ or US-6180958-\$ or US-6344663-\$ or US-5886368-\$ or US-5039354-\$ or US-4826778-\$ or US-6163066-\$ or US-6084248-\$ or US-6099574-\$ or US-5260560-\$ or US-5159424-\$ or US-5056897-\$ or US-5451798-\$ or US-5369040-\$ or US-6166319-\$ or US-6093937-\$ or US-6144581-\$ or US-5539217-\$ or US-5371383-\$ or US-5719410-\$ or US-5661312-\$ or US-5672889-\$ or US-5798548-\$ or US-5506421-\$).did. or (US-6562131-\$ or US-6547877-\$ or US-6562130-\$ or US-6537371-\$ or US-5030580-\$ or US-4189826-\$ or US-5932902-\$ or US-4598305-\$ or US-5449925-\$ or US-5441901-\$ or US-6236590-\$ or US-4462150-\$ or US-4460670-\$ or US-4657699-\$ or US-5604357-\$ or US-5580380-\$ or US-5623442-\$ or US-5654208-\$ or US-5670790-\$ or US-5714766-\$ or US-5740104-\$ or US-5754477-\$ or US-5786250-\$ or US-5789276-\$ or US-5846859-\$ or US-5877041-\$ or US-5907775-\$).did. or (US-6034001-\$ or US-5886379-\$ or US-5557122-\$ or US-5866930-\$ or US-5808336-\$ or US-5508543-\$ or US-5898197-\$ or US-6351411-\$ or US-6178112-\$ or US-6205052-\$ or US-6197439-\$ or US-5640343-\$ or US-5793697-\$ or US-6166948-\$ or US-6307775-\$ or US-4451391-\$ or US-4768072-\$ or US-6309907-\$ or US-5061976-\$ or US-5625217-\$ or US-6002143-\$ or US-5852306-\$ or US-6108177-\$ or US-5408377-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$).did. or (US-5293560-\$ or US-5298796-\$ or US-5407845-\$ or US-5415126-\$ or US-5455432-\$ or US-5477485-\$ or US-5530581-\$ or US-5557114-\$ or US-5562769-\$ or US-4841349-\$ or US-4893273-\$ or US-5049950-\$ or US-5111430-\$ or US-4738729-\$ or US-4769686-\$).did. or (US-20010032997-\$ or US-20010049183-\$ or US-20020024050-\$ or US-20020137284-\$ or US-20020036331-\$ or US-20020017647-\$ or US-20020041514-\$ or US-20030001191-\$).did. or (EP-291951-\$ or EP-681333-\$ or US-5585986-\$).did. or (JP-63289960-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-63181473-\$ or JP-62122275-\$ or JP-04056769-\$ or JP-03222367-\$ or JP-02203564-\$ or JP-56056677-\$ or JP-06302828-\$ or JP-07226507-\$ or JP-08255878-\$ or JP-60184681-\$ or JP-60242678-\$ or JP-06224431-\$ or JP-57126175-\$ or JP-04061170-\$).did. or | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2003/08/20 12:07 |
| Search History | 9/27/04 4:59:49 PM | | | |
| H:\EASTBACK\09691004 | JP-57126175-\$ or JP-04061170-\$).did. or | | | |

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|---|--------|--|---|------------------|
| - | 0 | ultra-amorphous near6 nanocrystalline | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2003/08/20 12:08 |
| - | 0 | ultra-amorphous | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2003/08/20 12:08 |
| - | 0 | ultra adj amorphous | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2003/08/20 12:08 |
| - | 26 | carbon adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/20 12:46 |
| - | 4 | (carbon adj gate "carbon gate") and float\$3 near4 gate and control adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/20 13:04 |
| - | 2 | ("4598305").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/20 13:04 |
| - | 2 | ("4994401").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2003/08/20 13:04 |
| - | 439692 | SiC "Si.sub."? "C.sub."? silicon adj carbide near6 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 10:29 |
| - | 5855 | (SiC "Si.sub."? "C.sub."? silicon adj carbide) near6 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 10:29 |
| - | 935 | (SiC "Si.sub."? "C.sub."? silicon adj carbide) near6 gate and barrier | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 10:30 |
| - | 74 | (SiC "Si.sub."? "C.sub."? silicon adj carbide) near4 gate and barrier and electron adj affinity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 13:17 |
| - | 74 | (SiC "Si.sub."? "C.sub."? silicon adj carbide "SiC.sub.2") near4 gate and barrier and electron adj affinity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 13:19 |
| - | 0 | "SiC.sub.2" near4 gate and barrier and electron adj affinity | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 13:20 |
| - | 1 | "SiC.sub.2" near4 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 13:20 |
| - | 30 | ("SiC.sub.2" carbon near4 (doping doped dopant) near4 (silicon adj carbide SiC)) and gate and (transistor MOSFET MOS NMOS NMOSFET PMOSFET field adj effect adj transistor) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 14:44 |

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| - | 2 | ("6770918").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 15:01 |
| - | 0 | "SiC.sub.2" near6 gate adj insulat\$3 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 15:02 |
| - | 1 | "SiC.sub.2" near6 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 15:02 |
| - | 0 | silicon adj dicarbide and gate and silicon adj dioxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 16:24 |
| - | 8 | ("SiC.sub.2" SiC2 silicon adj dicarbide) and gate and silicon adj dioxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:00 |
| - | 1 | first adj gate adj insulat\$3 and second adj gate adj insulat\$3 and "SiC.sub.2" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 16:32 |
| - | 1 | first adj gate adj insulat\$3 and second adj gate adj insulat\$3 and (SiC2 "SiC.sub.2") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 16:34 |
| - | 38 | barrier near4 silicon adj carbide same gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 16:43 |
| - | 0 | (multiple adj gate adj insulat\$3 adj (film layer)) near4 (silicon carbide silicon adj dicarbide SiC2 "Si C.sub.2" "SiC.sub.2") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 16:46 |
| - | 7 | ("SiC.sub.2" SiC2 silicon adj dicarbide) and gate and silicon adj dioxide and "SiO.sub.2" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:01 |
| - | 340 | "SiC.sub.2" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:01 |
| - | 27 | "SiC.sub.2" and gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:01 |
| - | 1 | "SiC.sub.2" near4 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:02 |
| - | 5 | "SiC.sub.2" same gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:10 |

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| - | 2 | ("5369040").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:13 |
| - | 2 | 903452.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:14 |
| - | 6 | 256643.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:17 |
| - | 7 | 652068.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:17 |
| - | 4 | 652420.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:22 |
| - | 3 | 903486.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:25 |
| - | 5 | 259870.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 17:34 |
| - | 5 | 259870.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 18:25 |
| - | 38 | carbon adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 18:26 |
| - | 7 | carbon adj gate and floating adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 18:28 |
| - | 7 | "carbon gate" and floating adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 18:38 |
| - | 0 | carbon-gate near4 ISFET | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 18:38 |
| - | 0 | carbon-gate near4 pH-ISFET | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 18:38 |
| - | 0 | carbon near4 gate near4 pH-ISFET | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/24 18:39 |

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| - | 11 | carbon near4 gate and pH-ISFET | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/24 18:40 |
| - | 11 | carbon near8 gate and pH-ISFET | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/24 18:40 |
| - | 19 | carbon and gate and pH-ISFET | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/24 18:42 |
| - | 23145 | (carbon C) near8 gate and (pH-ISFET MOSFET transistor CMOSFET MOS CMOS) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/24 18:44 |
| - | 51 | carbon near8 gate and nanotube and field adj effect | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/24 18:44 |
| - | 552 | gate near4 (C carbon) near4 (silicon Si) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 13:04 |
| - | 19 | gate near4 (C carbon) near4 (silicon Si) near4 (doped doping) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 13:06 |
| - | 19 | gate near4 ("C" carbon) near4 (silicon Si) near4 (doped doping) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 13:10 |
| - | 257 | carbon near5 gate and (257/\$9.ccls. 438/\$9.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 13:11 |
| - | 161 | carbon near3 gate and (257/\$9.ccls. 438/\$9.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 13:15 |
| - | 2 | 5061976.pn. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 13:13 |
| - | 0 | Si-doped near4 carbon near3 gate and (257/\$9.ccls. 438/\$9.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 13:16 |
| - | 10 | doped near4 carbon near3 gate and (257/\$9.ccls. 438/\$9.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 13:16 |
| - | 2 | (silicon si) near4 doped near4 carbon near3 gate and (257/\$9.ccls. 438/\$9.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 13:17 |

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| - | 66958 | silicon and (anneal annealing) carbon near3 gate and (257/\$9.ccls. 438/\$9.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 13:18 |
| - | 1 | silicon and (anneal annealing) near4 carbon near4 gate and (257/\$9.ccls. 438/\$9.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 13:19 |
| - | 4 | silicon near4 (doped doping) near4 carbon near4 gate and (257/\$9.ccls. 438/\$9.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 13:20 |
| - | 7 | silicon near4 (doped doping) near4 carbon near4 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 13:25 |
| - | 0 | "C:Si" near4 gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 13:25 |
| - | 64 | "C:Si" | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 13:26 |
| - | 7 | "C:Si" and gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 13:35 |
| - | 4 | 691004.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 13:36 |
| - | 2 | 903452.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 13:37 |
| - | 4 | 652420.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 13:37 |
| - | 1 | ("5369040").PN. | USPAT | 2004/09/25 14:17 |
| - | 542 | floating near2 gate and control near2 gate and ((Si silicon) near2 (C carbon) silicon adj carbide "Si.sub."\$2"C.sub."\$2 silicon-doped adj carbon carbon-doped adj silicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 14:23 |
| - | 151 | floating near2 gate and control near2 gate and ((Si silicon) near2 (carbon) silicon adj carbide "Si.sub."\$2"C.sub."\$2 silicon-doped adj carbon carbon-doped adj silicon) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 16:04 |
| - | 2 | ("5801401").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 16:04 |

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| - | 223 | (US-4893273-\$ or US-4841349-\$ or US-4769686-\$ or US-4738729-\$ or US-4657699-\$ or US-4462150-\$ or US-4460670-\$ or US-6125062-\$ or US-6002143-\$ or US-5852306-\$ or US-5449925-\$ or US-6301162-\$ or US-6222778-\$ or US-4426764-\$ or US-6562131-\$ or US-6547877-\$ or US-6562130-\$ or US-6537371-\$ or US-5030580-\$ or US-5907775-\$ or US-5886379-\$ or US-5877041-\$ or US-5846859-\$ or US-5789276-\$ or US-5786250-\$ or US-5754477-\$).did. or (US-5740104-\$ or US-5714766-\$ or US-5670790-\$ or US-5654208-\$ or US-5623442-\$ or US-5604357-\$ or US-5580380-\$ or US-5562769-\$ or US-5557114-\$ or US-5530581-\$ or US-5477485-\$ or US-5455432-\$ or US-5415126-\$ or US-5407845-\$ or US-5298796-\$ or US-5293560-\$ or US-5260593-\$ or US-5235195-\$ or US-5145741-\$ or US-5111430-\$ or US-5049950-\$ or US-5672889-\$ or US-5661312-\$ or US-5539217-\$ or US-5506421-\$ or US-5465249-\$ or US-5323040-\$).did. or (US-4507673-\$ or US-6018166-\$ or US-5625217-\$ or US-5061976-\$ or US-4943838-\$ or US-6309907-\$ or US-4768072-\$ or US-4451391-\$ or US-6307775-\$ or US-6351411-\$ or US-5898197-\$ or US-5508543-\$ or US-5808336-\$ or US-5866930-\$ or US-5557122-\$ or US-6034001-\$ or US-5393999-\$ or US-6383576-\$ or US-6166319-\$ or US-5734181-\$ or US-5451798-\$ or US-5369040-\$ or US-5260560-\$ or US-5159424-\$ or US-5056897-\$ or US-5039354-\$ or US-4826778-\$).did. or (US-5886368-\$ or US-5719410-\$ or US-5371383-\$ or US-6365919-\$ or US-6313482-\$ or US-6306691-\$ or US-6297521-\$ or US-6249020-\$ or US-6133587-\$ or US-6121633-\$ or US-6075259-\$ or US-6049110-\$ or US-6011279-\$ or US-5798548-\$ or US-6099574-\$ or US-6093937-\$ or US-6084248-\$ or US-4473836-\$ or US-4113515-\$ or US-4849797-\$ or US-6344663-\$ or US-6180958-\$ or US-6133120-\$ or US-5989958-\$ or US-5801401-\$ or US-5629222-\$ or US-5449941-\$).did. or (US-6144581-\$ or US-6130147-\$ or US-6031263-\$ or US-5976926-\$ or US-5858811-\$ or US-5698869-\$ or US-4994401-\$ or US-6166401-\$ or US-6163066-\$ or US-4598305-\$ or US-5932902-\$ or US-4373167-\$ or US-4189826-\$ or US-6492694-\$ or US-6723581-\$ or US-6141260-\$ or US-6304493-\$ or US-6297994-\$ or US-6407426-\$ or US-6452831-\$ or US-6452839-\$ or US-6465375-\$ or US-6514820-\$ or US-6563260-\$ or US-6731531-\$ or US-6734510-\$ or US-6746893-\$).did. or (US-6754108-\$ or US-6762068-\$ or US-6778441-\$ or US-6781876-\$ or US-6794255-\$ or US-6573169-\$ or US-6586797-\$ or US-5441901-\$ or US-6300193-\$ or US-6407424-\$ or US-6630375-\$ or US-6746921-\$ or US-6197439-\$ or US-5640343-\$ or US-5793697-\$ or US-6166948-\$ or | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/25 18:18 |
| Search History | 9/27/04 4:49 PM | Page 40 | | |
| H:\EASTBACK\09691004 | USD | | | |

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|---|----|---|---|------------------|
| - | 47 | control adj (gates gate) and floating adj (gates gate) near4 (silicon adj carbide "SiC") | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 17:30 |
| - | 2 | 6309907.pn. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 17:32 |
| - | 2 | ("5886368").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 17:42 |
| - | 3 | 902843.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 17:49 |
| - | 23 | ((("4598305") or ("4980303") or ("4994401") or ("5189504") or ("5336361") or ("5367306") or ("5409501") or ("5990531") or ("6100193") or ("6166768") or ("6365919")).PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 17:51 |
| - | 25 | ((("4598305") or ("4980303") or ("4994401") or ("5189504") or ("5336361") or ("5367306") or ("5409501") or ("5990531") or ("6100193") or ("6166768") or ("6365919") or ("5471515")).PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 17:51 |
| - | 1 | 135413.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/25 18:19 |
| - | 7 | 134713.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/25 18:22 |
| - | 33 | "6031263" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/25 18:23 |
| - | 2 | ("6031263").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 18:24 |
| - | 2 | ("6307775").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 18:24 |
| - | 2 | ("6249020").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 18:29 |
| - | 16 | ((("5798548") or ("5808336") or ("5828101") or ("5861346") or ("5886376") or ("5976926") or ("5989958") or ("5990531") or ("6084248") or ("6093937") or ("6099574") or ("6100193") or ("6130147") or ("6166768") or ("6271566") or ("6365919")).PN. | USPAT | 2004/09/25 18:34 |
| - | 2 | 902133.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/25 18:38 |

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| - | 6 | ((("5336361") or ("5990531") or ("6166768"))).PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:05 |
| - | 4 | ((("5910665") or ("6049091"))).PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 18:55 |
| - | 3 | 231687.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 18:56 |

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|----------------------|--------------------|---|---|------------------|
| - | 233 | (US-4598305-\$ or US-5441901-\$ or US-6108177-\$ or US-5408377-\$ or US-6205052-\$ or US-6563260-\$ or US-6514820-\$ or US-6734510-\$ or US-6731531-\$ or US-6178112-\$ or US-6236590-\$ or US-6166948-\$ or US-5793697-\$ or US-5640343-\$ or US-6197439-\$ or US-6465375-\$ or US-6452839-\$ or US-6452831-\$ or US-6723581-\$ or US-6492694-\$ or US-4189826-\$ or US-4373167-\$ or US-5932902-\$ or US-6407426-\$ or US-6297994-\$ or US-6304493-\$).did. or (US-6141260-\$ or US-5910665-\$ or US-5861346-\$ or US-5336361-\$ or US-6049091-\$ or US-5828101-\$ or US-5990531-\$ or US-6100193-\$ or US-6300193-\$ or US-5886376-\$ or US-5959896-\$ or US-6407424-\$ or US-6246606-\$ or US-6746921-\$ or US-6630375-\$ or US-6140181-\$ or US-6271566-\$ or US-6166768-\$ or US-5061976-\$ or US-4943838-\$ or US-6309907-\$ or US-4768072-\$ or US-4451391-\$ or US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5654208-\$).did. or (US-5670790-\$ or US-5714766-\$ or US-6778441-\$ or US-6781876-\$ or US-6762068-\$ or US-6794255-\$ or US-5719410-\$ or US-5371383-\$ or US-6365919-\$ or US-6313482-\$ or US-6306691-\$ or US-6297521-\$ or US-6249020-\$ or US-6133587-\$ or US-6121633-\$ or US-6075259-\$ or US-6049110-\$ or US-6011279-\$ or US-5798548-\$ or US-5672889-\$ or US-5661312-\$ or US-5539217-\$ or US-5506421-\$ or US-5465249-\$ or US-5323040-\$ or US-4507673-\$ or US-6018166-\$).did. or (US-5625217-\$ or US-4849797-\$ or US-6344663-\$ or US-6180958-\$ or US-6133120-\$ or US-5989958-\$ or US-5801401-\$ or US-5629222-\$ or US-5449941-\$ or US-5393999-\$ or US-6383576-\$ or US-6166319-\$ or US-5734181-\$ or US-5451798-\$ or US-5369040-\$ or US-5260560-\$ or US-5159424-\$ or US-5056897-\$ or US-5039354-\$ or US-4826778-\$ or US-5886368-\$ or US-6099574-\$ or US-6144581-\$ or US-6166401-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$).did. or (US-6093937-\$ or US-5858811-\$ or US-5698869-\$ or US-4113515-\$ or US-4473836-\$ or US-6163066-\$ or US-6130147-\$ or US-6573169-\$ or US-6586797-\$ or US-5449925-\$ or US-4738729-\$ or US-4769686-\$ or US-4841349-\$ or US-4893273-\$ or US-5049950-\$ or US-5111430-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$ or US-5293560-\$ or US-5298796-\$ or US-5407845-\$ or US-5415126-\$ or US-5455432-\$ or US-5477485-\$ or US-5530581-\$ or US-5557114-\$).did. or (US-6754108-\$ or US-5562769-\$ or US-6746893-\$ or US-4994401-\$ or US-5030580-\$ or US-6537371-\$ or US-6562130-\$ or US-6547877-\$ or US-6562131-\$ or US-4426764-\$ or US-6222778-\$ or US-6201162-\$ or US-4657699-\$ or US-4462150-\$ or US-5846859-\$ or US-5877041-\$ or | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/25 19:01 |
| Search History | 9/27/04 4:59:49 PM | Page 43 | | |
| H:\EASTBACK\09691004 | USD | | | |

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|---|-----|--|---|------------------|
| - | 0 | carbon-doped near4 silicon near4 floating adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:01 |
| - | 0 | carbon near4 (doped dopant) near4 silicon near4 floating adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:03 |
| - | 0 | c-doped near4 silicon near4 floating adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:03 |
| - | 2 | ("6746893").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:19 |
| - | 2 | ("6762068").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:22 |
| - | 2 | ("5949483").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:33 |
| - | 0 | micron.as. and floating.clm. and (reset control).clm. and "Si.sub."\$2"C.sub."\$2.clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:35 |
| - | 145 | micron.as. and floating.clm. and (reset control).clm. and (silicon carbide "Si.sub."\$2"C.sub."\$2).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:36 |
| - | 4 | 902132.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:40 |
| - | 5 | 259870.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:45 |
| - | 7 | 138294.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 19:58 |
| - | 2 | ("5886368").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 20:22 |
| - | 0 | ("903453.ap.").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 20:23 |
| - | 3 | 903453.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/25 20:23 |

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|----------------------|--------------------|---|---|------------------|
| - | 233 | (US-6762068-\$ or US-6778441-\$ or US-6746893-\$ or US-6746921-\$ or US-6731531-\$ or US-6734510-\$ or US-6723581-\$ or US-6630375-\$ or US-6586797-\$ or US-6573169-\$ or US-6563260-\$ or US-6547877-\$ or US-6562130-\$ or US-6537371-\$ or US-6562131-\$ or US-6492694-\$ or US-6514820-\$ or US-6452839-\$ or US-6465375-\$ or US-6383576-\$ or US-6407424-\$ or US-6407426-\$ or US-6452831-\$ or US-6351411-\$ or US-6365919-\$ or US-6344663-\$).did. or (US-6309907-\$ or US-6313482-\$ or US-6307775-\$ or US-6306691-\$ or US-6297994-\$ or US-6300193-\$ or US-6301162-\$ or US-6304493-\$ or US-6249020-\$ or US-6297521-\$ or US-6205052-\$ or US-6222778-\$ or US-6236590-\$ or US-6246606-\$ or US-6180958-\$ or US-6197439-\$ or US-6794255-\$ or US-6781876-\$ or US-4738729-\$ or US-4768072-\$ or US-4507673-\$ or US-4598305-\$ or US-4657699-\$ or US-4462150-\$ or US-5056897-\$ or US-4994401-\$ or US-5039354-\$).did. or (US-4473836-\$ or US-4460670-\$ or US-4113515-\$ or US-4189826-\$ or US-4373167-\$ or US-4426764-\$ or US-4451391-\$ or US-6100193-\$ or US-5990531-\$ or US-6166768-\$ or US-5336361-\$ or US-6271566-\$ or US-6049091-\$ or US-5861346-\$ or US-5828101-\$ or US-5910665-\$ or US-4849797-\$ or US-4893273-\$ or US-4769686-\$ or US-4826778-\$ or US-5030580-\$ or US-4943838-\$ or US-4841349-\$ or US-5049950-\$ or US-5623442-\$ or US-5530581-\$ or US-5539217-\$).did. or (US-5557114-\$ or US-5557122-\$ or US-5506421-\$ or US-5508543-\$ or US-5455432-\$ or US-5465249-\$ or US-5477485-\$ or US-5449941-\$ or US-5451798-\$ or US-5407845-\$ or US-5408377-\$ or US-5415126-\$ or US-5441901-\$ or US-5449925-\$ or US-6099574-\$ or US-6108177-\$ or US-5369040-\$ or US-5393999-\$ or US-5371383-\$ or US-5323040-\$ or US-5298796-\$ or US-5293560-\$ or US-5260560-\$ or US-5260593-\$ or US-5159424-\$ or US-5235195-\$ or US-5145741-\$).did. or (US-5061976-\$ or US-5111430-\$ or US-6133120-\$ or US-5976926-\$ or US-5907775-\$ or US-5932902-\$ or US-5852306-\$ or US-5858811-\$ or US-5866930-\$ or US-5798548-\$ or US-5801401-\$ or US-6049110-\$ or US-6075259-\$ or US-5989958-\$ or US-6002143-\$ or US-6011279-\$ or US-5886379-\$ or US-5898197-\$ or US-5877041-\$ or US-6034001-\$ or US-6031263-\$ or US-6018166-\$ or US-6093937-\$ or US-6084248-\$ or US-6130147-\$ or US-5959896-\$ or US-5886368-\$).did. or (US-5886376-\$ or US-5670790-\$ or US-5672889-\$ or US-5698869-\$ or US-5714766-\$ or US-5640343-\$ or US-5654208-\$ or US-5661312-\$ or US-5625217-\$ or US-5629222-\$ or US-5562769-\$ or US-5580380-\$ or US-5604357-\$ or US-5608336-\$ or US-5846859-\$ or US-5786250-\$ or | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/27 07:36 |
| Search History | 9/27/04 4:58:49 PM | | | |
| H:\EASTBACK\09691004 | USP | | | |

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|---|-----|--|---|------------------|
| - | 19 | carbon near4 gate and floating adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 08:18 |
| - | 2 | ("6309907").PN. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 08:26 |
| - | 0 | floating adj gate and control adj gate and silicon adj dioxide near3 (interlayer adj dielectric ild) and mosfet | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 08:31 |
| - | 0 | floating adj gate and silicon adj dioxide near3 (interlayer adj dielectric ild) and mosfet | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 08:31 |
| - | 34 | floating adj gate and silicon adj dioxide and (interlayer adj dielectric ild) and mosfet | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 09:18 |
| - | 4 | 691004.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 10:54 |
| - | 170 | floating adj gate and control adj gate and (silicon adj carbide SiC) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 10:55 |
| - | 47 | floating adj gate near4 (silicon adj carbide SiC) and control adj gate and (memory eeprom) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 11:05 |
| - | 52 | floating adj gate near4 (silicon adj carbide SiC) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 11:05 |
| - | 5 | floating adj gate near4 (silicon adj carbide SiC) not (floating adj gate near4 (silicon adj carbide SiC) and control adj gate and (memory eeprom)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 11:10 |
| - | 2 | 903452.ap. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 11:11 |
| - | 5 | 746893.pn. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 11:11 |
| - | 2 | 6746893.pn. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 13:41 |
| - | 0 | eprom near5 (p-type n-type) near5 (preferabl\$1 advantage\$3) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/27 13:42 |

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|---|-----|--|---|------------------|
| - | 5 | floating adj gate near5 (p-type n-type) near5 (preferabl\$1 advantage\$3) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/27 13:44 |
| - | 94 | channel near5 (p-type n-type) near5 (preferabl\$1 advantage\$3) | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/27 13:48 |
| - | 23 | channel near5 (p-type n-type) near5 (preferabl\$1 advantage\$3) and (eprom memory) | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/27 13:57 |
| - | 24 | channel near5 (p-type n-type) near5 (preferabl\$1 advantage\$3) and (floating adj gate eprom memory) | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/27 13:58 |
| - | 7 | channel near5 (p-type n-type) near5 (preferabl\$1 advantage\$3) and floating adj gate | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/27 14:03 |
| - | 2 | ("4173766").PN. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/27 14:06 |
| - | 0 | ("floatingadjgateand(cmoscmosfet)").PN. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/27 14:06 |
| - | 478 | floating adj gate.ti,ab,clm. and (cmos cmosfet).ti,ab,clm. | USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2004/09/27 15:22 |